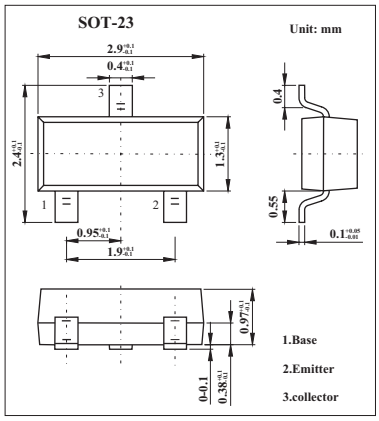
# Silicon NPN Epitaxial

# 2SC2618




## ■ Features

● Low frequency amplifier.

## ■ Absolute Maximum Ratings Ta = 25℃

| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Collector-base voltage | $V_{CBO}$ | 35 | V |
| Collector-emitter voltage | $V_{CEO}$ | 35 | V |
| Emitter-base voltage | $V_{EBO}$ | 4 | V |
| Collector current | $I_C$ | 500 | mA |
| Collector dissipation | $P_C$ | 150 | mW |
| Junction temperature | $T_j$ | 150 | ℃ |
| Storage temperature | $T_{stg}$ | -55 to +150 | ℃ |

## ■ Electrical Characteristics Ta = 25℃

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C$ = 10μA , $I_E$ = 0 | 35 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C$ = 1mA , $R_{BE}$ = ∞ | 35 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E$ = 10μA , $I_C$ = 0 | 4 | | | V |
| Collector cutoff current | $I_{CBO}$ | $V_{CB}$ = 20V, $I_C$ = 0 | | | 0.5 | μA |
| DC current gain | $h_{FE}1$ | $V_{CE}$ = 3V , $I_C$ = 10mA | 100 | | 320 | |
| | $h_{FE}2$ | $V_{CE}$ = 3V , $I_C$ = 500mA | 10 | | | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C$ = 150mA , $I_B$ = 15mA | | 0.2 | 0.6 | V |
| Base-emitter voltage | $V_{BE}$ | $V_{CE}$ = 3V , $I_C$ = 10mA | | 0.64 | | V |

## ■ $h_{FE}$ Classification

| Marking | RC | RD |
|---|---|---|
| hFE | 100～200 | 160～320 |